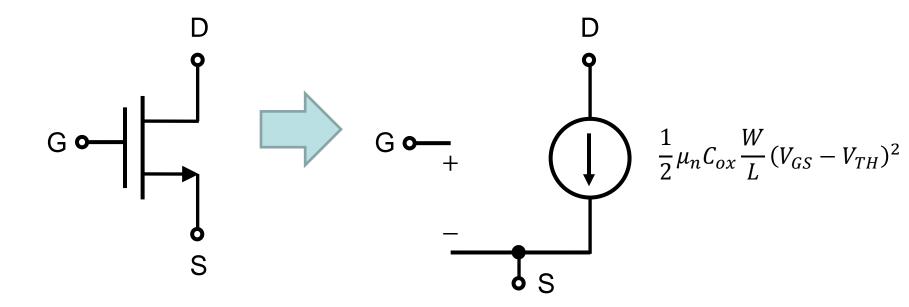
# Lecture13: MOSFET, small-signal model

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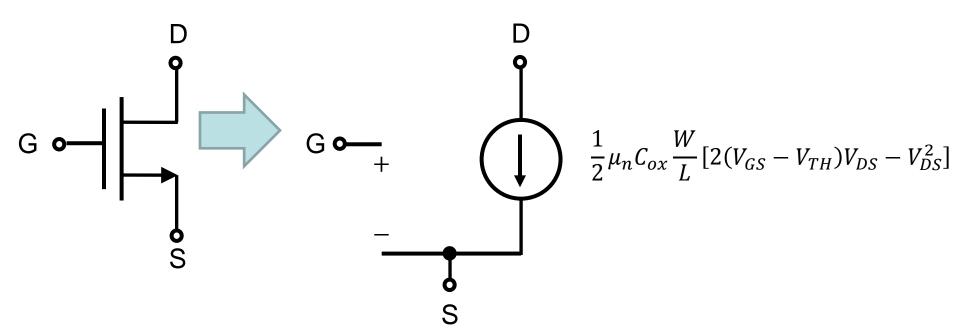
# Large-signal model (1/2)

- Saturation region
  - Drain current is determined by gate voltage. (voltage-controlled current source)



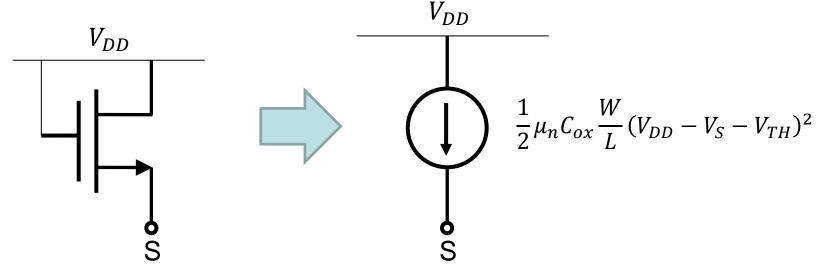
# Large-signal model (2/2)

- Triode region
  - Still, it can be described by a voltage-controlled current source.



### Example 6.13 (Razavi)

- Always in the saturation region!
  - Any necessary condition?

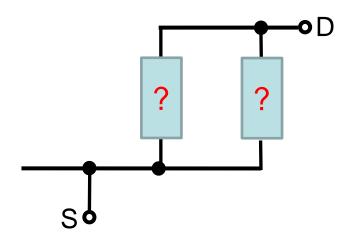


Gate and drain are tied.

They are connected to  $V_{DD}$ .

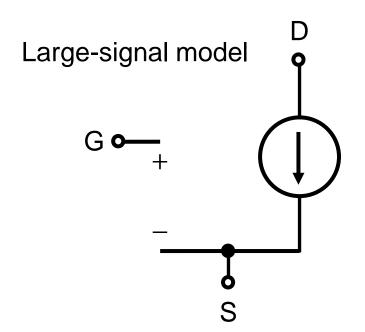
# **Small-signal current**

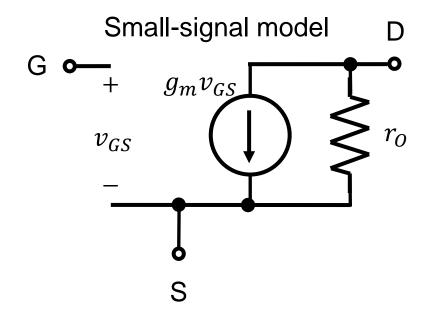
- Using the transconductance  $(g_m)$  and the output resistance  $(r_O)$ ,
  - The small-signal drain current is given as  $i_D = g_m v_G + \frac{v_D}{r_O}$ .
  - When we build a small-signal model, two contributions must be separately considered.



# **Small-signal model**

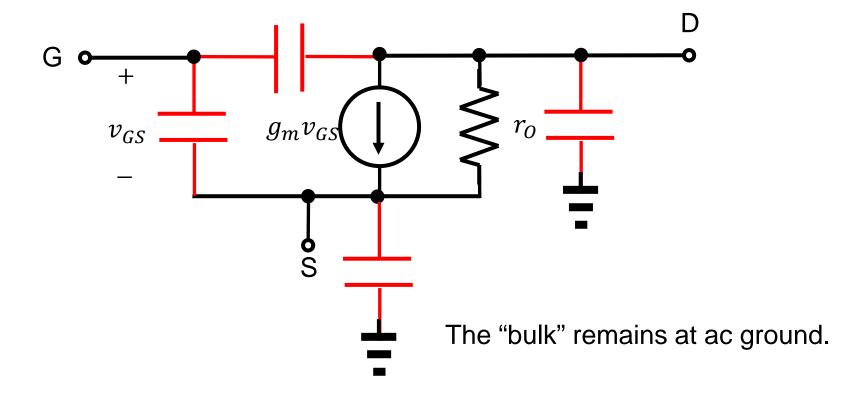
 For small-signal analysis, a small-signal model for the MOSFET is introduced.





### Time-dependent one?

In general, capacitive components can be seen.

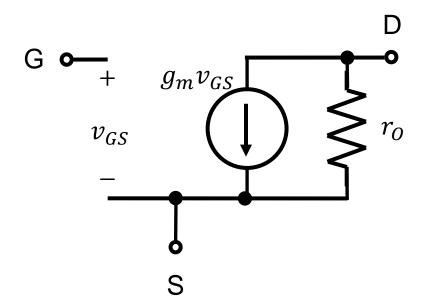


#### At low frequencies

- Capacitor current is  $I = C \frac{dV}{dt}$ .
  - When a sinusoidal dependence, for example  $\sin \omega t$ , is assumed, the capacitor current is proportional to  $\omega$ .
  - At low frequencies,  $\omega$  can be regarded as a small number.
  - In other words, the electric conduction between two nodes becomes rather weak.
  - Therefore, we often neglect the capacitive components in the small-signal model.
  - Of course, at higher frequencies, they become very important.

### **Small-signal MOSFET model**

- Small-signal MOSFET model
  - Two branches are related with two partial derivatives.



# Simple math

- Following relations are useful.
  - Sine and cosine functions can be expanded with  $e^{+j\omega t}$  and  $e^{-j\omega t}$ .

$$\sin \omega t = -\frac{j}{2}e^{+j\omega t} + \frac{j}{2}e^{-j\omega t}$$
$$\cos \omega t = \frac{1}{2}e^{+j\omega t} + \frac{1}{2}e^{-j\omega t}$$

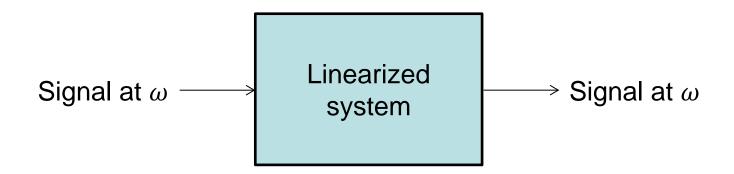
- Therefore, for a function of  $f(t) = f_s \sin \omega t + f_c \cos \omega t$ , the expansion is

$$f(t) = \left(-j\frac{f_s}{2} + \frac{f_c}{2}\right)e^{+j\omega t} + \left(+j\frac{f_s}{2} + \frac{f_c}{2}\right)e^{-j\omega t}$$

- A single complex number,  $-j\frac{f_s}{2} + \frac{f_c}{2}$ , is enough to represent f(t).

# Linearized system

- Our circuit is nonlinear in general.
- However, we have <u>linearized</u> it.
  - When the input signal has an angluar frequency,  $\omega$ , the output signal has the same one.
  - It is sufficient to consider the input-output relation at  $\omega$ .



#### **Impedance**

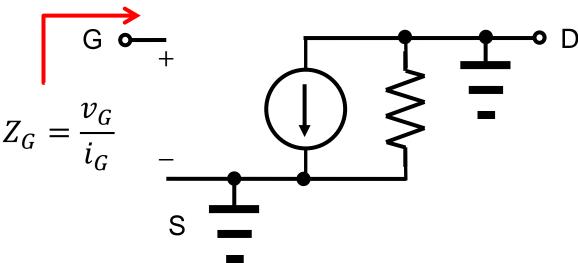
- Resistance, V(t) = R I(t)
  - It is assumed that V(t) and I(t) are in the same phase.
- Impedance,  $V(\omega) = Z(\omega)I(\omega)$ 
  - Consider  $V(t) = V_0 \sin \omega t$  and  $I(t) = I_0 \cos \omega t$ . (Different phases)
  - We introduce a phasor voltage,  $V(\omega)$ , and a phasor current,  $I(\omega)$ .
  - The relation between V(t) and  $V(\omega)$  is  $V(t) = Re[V(\omega)e^{j\omega t}]$ .
  - When  $V(t) = V_0 \sin \omega t$ , the phasor voltage is  $V(\omega) = -jV_0$ .
  - When  $I(t) = I_0 \cos \omega t$ , the phasor voltage is  $I(\omega) = I_0$ .
  - In this example,  $Z(\omega) = -j\frac{V_0}{I_0}$ . A purely imaginary number.

#### **Multi-terminal devices**

- When the number of terminals is 3,
  - We can define 9 (= 3 X 3) different impedances.
- Termination condition is important.
  - Depending on the termination condition, the impedance can be heavily changed.
  - In many cases, it is obvious from the problem.

### Impedances of MOSFET

- "Looking into the <u>TERMINAL</u>," we see the impedance of the <u>TERMINAL</u>.
  - Example) Looking into the gate. The source and drain are acgrounded.



Similar for other terminals